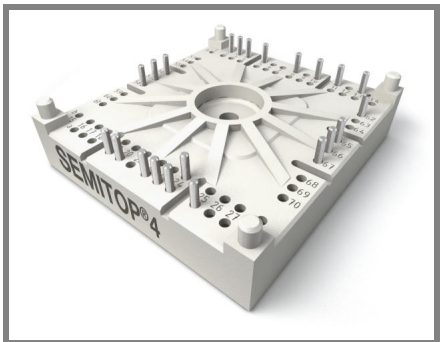
SK100GH128T



SEMITOP®4

IGBT module

SK100GH128T

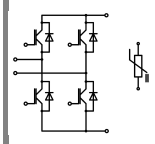
Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- SPT IGBT Technology
- CAL technology FWD
- Integrated NTC Temperature sensor

Typical Applications*

- Voltage regulator



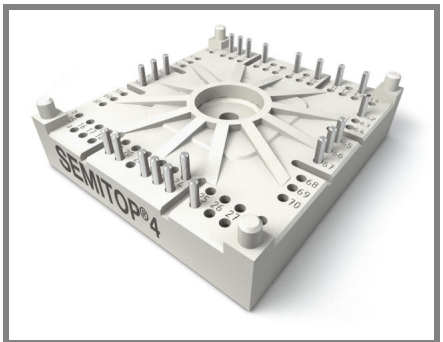
GH-T

Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 125 °C	T_s = 25 °C	120	A
		T_s = 70 °C	80	A
I_{CRM}	I_{CRM}= 2 x I_{Cnom} , $t_p \leq$ 1ms		200	A
V_{GES}			20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_s = 25 °C	67	A
		T_s = 70 °C	50	A
I_{FRM}	I_{FRM}= 2 x I_{Fnom} , $t_p \leq$ 1ms		110	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	550	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +150	°C
T_{stg}			-40 ... +125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics	T_c = 25 °C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,2	mA
		T_j = 125 °C		0,4		mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 125 °C			400	nA
V_{CE0}		T_j = 25 °C		1,1	1,3	V
		T_j = 125 °C		1	1,2	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		6		mΩ
		T_j = 125°C		11		mΩ
$V_{CE(sat)}$	I_{Cnom} = 100 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,9	2,3	V
		T_j = 125°C$_{chiplev.}$		2,1		V
C_{ies}				9		nF
C_{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,66		nF
C_{res}				0,42		nF
R_{Gint}	T_j = 25 °C			5		Ω
$t_{d(on)}$	R_{Gon} = 4 Ω	V_{CC} = 600V		80		ns
t_r				33		ns
E_{on}		I_C= 100A		5,97		mJ
$t_{d(off)}$	R_{Goff} = 4 Ω	T_j = 125 °C		418		ns
t_f	di/dt = 3000 A/µs			70		ns
E_{off}				8,5		mJ
$R_{th(j-s)}$	per IGBT			0,34		K/W

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SK100GH128T



SEMITOP®4

IGBT module

SK100GH128T

Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- SPT IGBT Technology
- CAL technology FWD
- Integrated NTC Temperature sensor

Typical Applications*

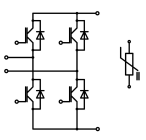
- Voltage regulator

Characteristics

Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 55 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8	2,3	V
V_{F0}		T_j = 125 °C		1,2		V
r_F		T_j = 125 °C		10,9		mΩ
I_{RRM}	I_F = 100 A	T_j = 125 °C		125		A
Q_{rr}	di/dt = 3000 A/µs			25		µC
E_{rr}	V_{CC}=600V			3,66		mJ
$R_{th(j-s)D}$	per diode			0,7	0,85	K/W
Freewheeling Diode						
$V_F = V_{EC}$	I_{Fnom} = A; V_{GE} = V	T_j = °$C_{chiplev.}$				V
V_{F0}		T_j = °C				V
r_F		T_j = °C				V
I_{RRM}	I_F = A	T_j = °C				A
Q_{rr}						µC
E_{rr}						mJ
	per diode					K/W
M_s	to heat sink		2,5		2,75	Nm
w				60		g
Temperature sensor						
R_{100}	T_s= 100°C (R_{25}=5kΩ)			493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



GH-T

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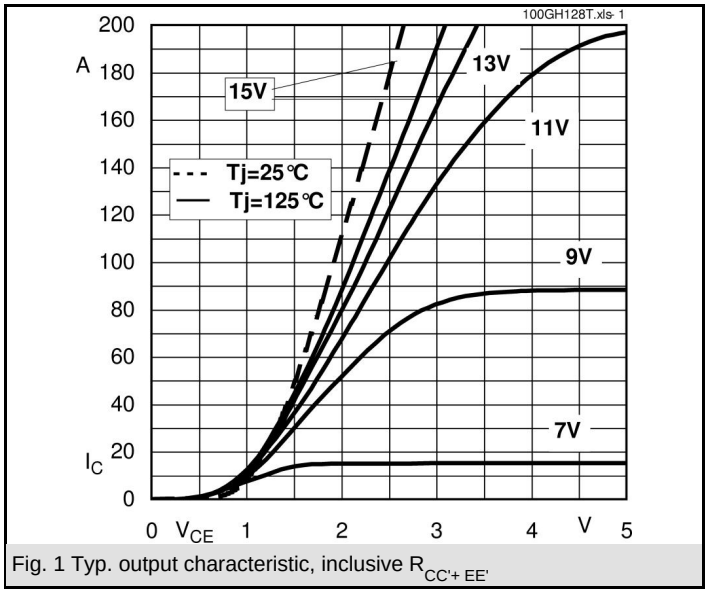


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

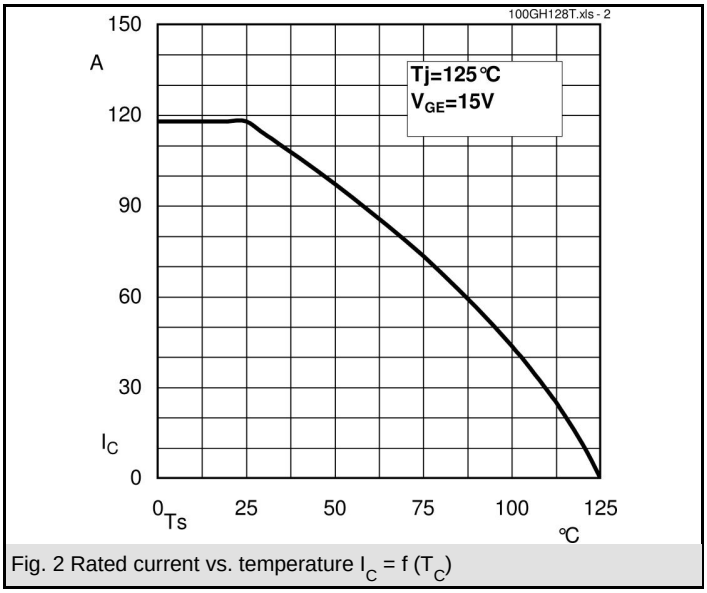


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

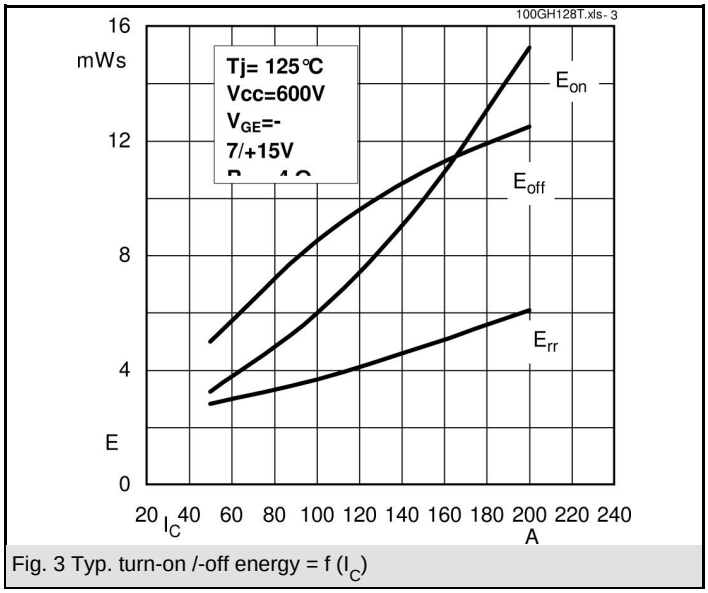


Fig. 3 Typ. turn-on /-off energy = f (I_C)

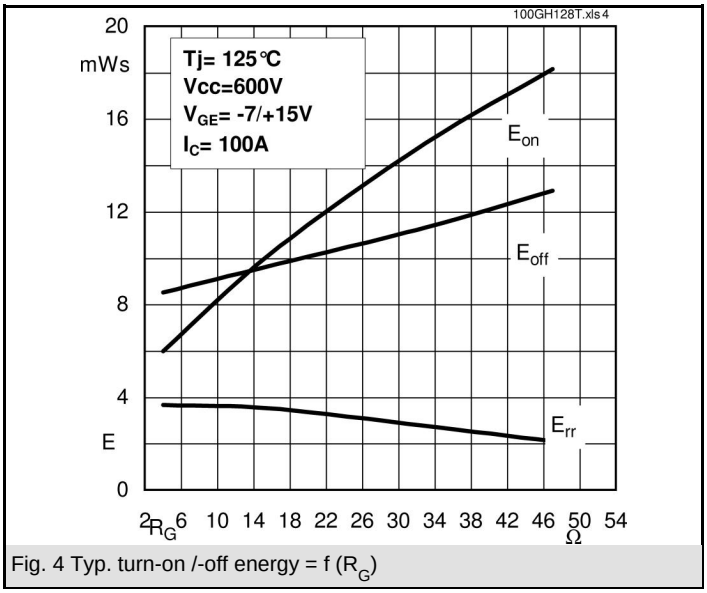


Fig. 4 Typ. turn-on /-off energy = f (R_G)

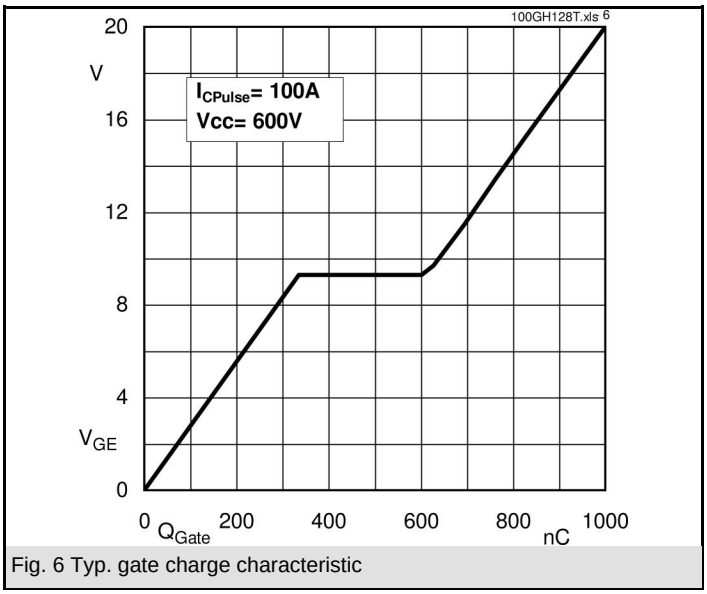


Fig. 6 Typ. gate charge characteristic

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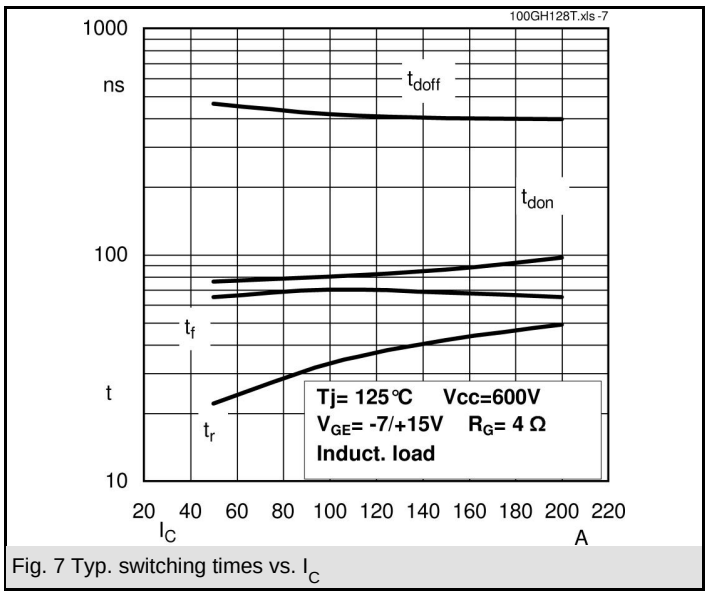


Fig. 7 Typ. switching times vs. I_C

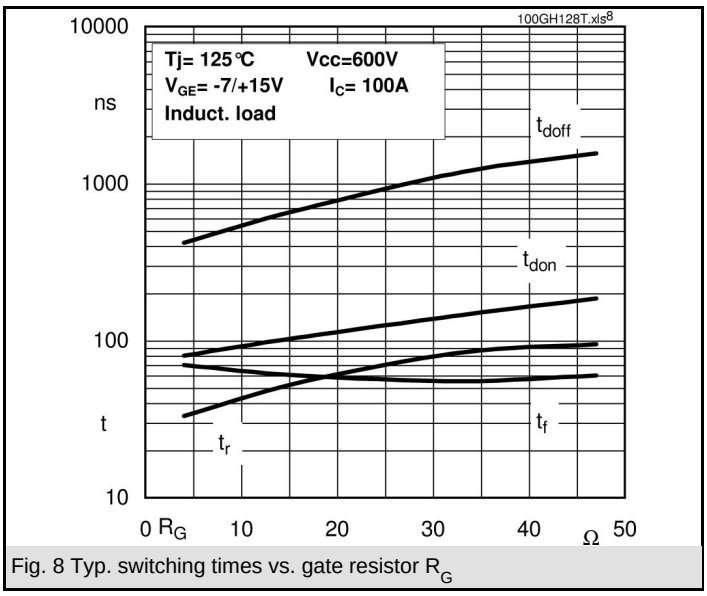


Fig. 8 Typ. switching times vs. gate resistor R_G

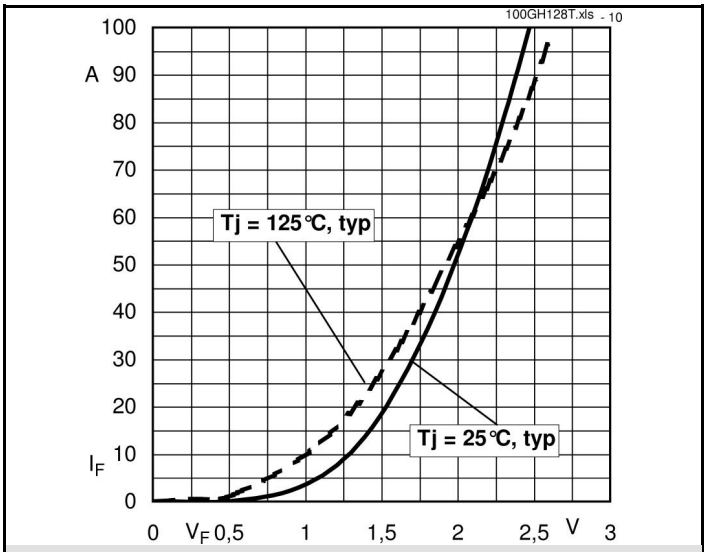
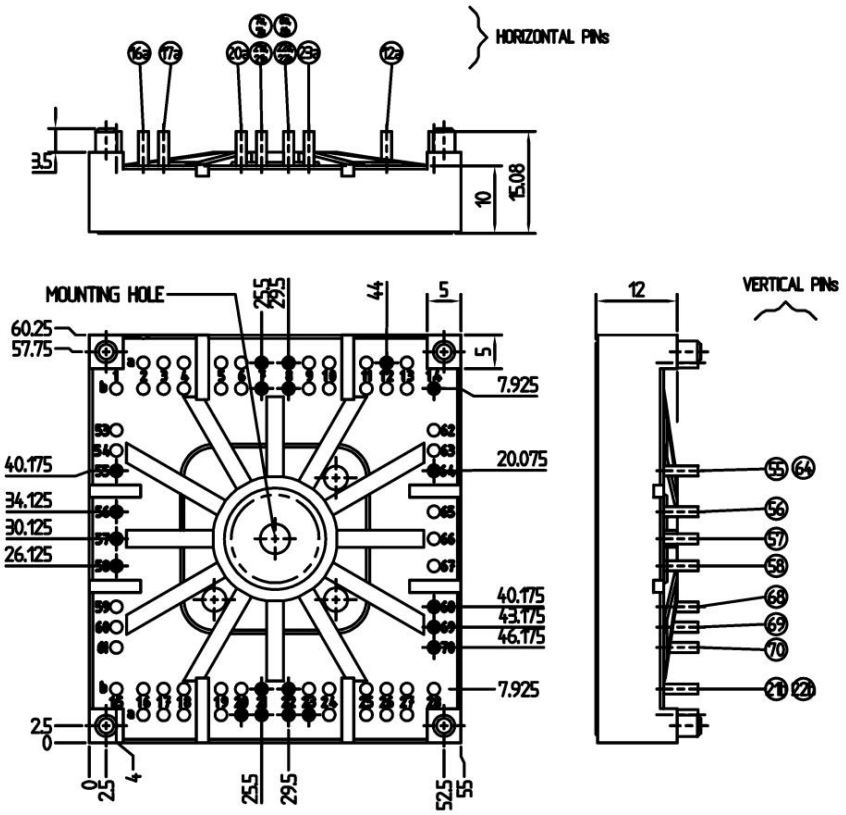


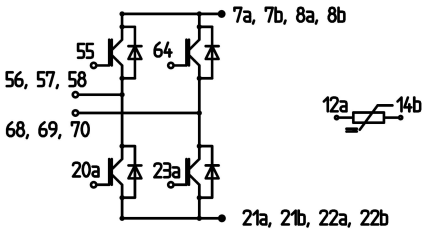
Fig. 10 CAL diode forward characteristic

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UL recognized file no. E 63 532



Case T84 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 84 GH-T

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